



### Solvent Bench

### Acid/Alkaline Bench

## Nanofabrication CORE Facility

# RUTGERS

#### **Standard Processes**

- RCA SC1/SC2 at 75-80 °C
  - Surface clean
- Piranha Solution  $(H_2SO_4 + H_2O_2)$ 
  - Photoresist and organic materials removal
- BOE Oxide Etch 10:1
  - Etching dielectric layers: SiO<sub>x</sub>, SiN<sub>x</sub>, etc.
- TMAH Silicon Etch (25 aq. wt%)
  - Etching crystalline silicon



#### **Piranha Cleaning**

#### Acids

- Hydrochloric Acid HCL
- Buffered Oxide Etch BOE 10:1
- Hydrofluoric Acid HF 49%
- Sulfuric Acid 96% H<sub>2</sub>SO<sub>4</sub>
- Nitric Acid HNO<sub>3</sub>
- Metal Etchants (Au, Al, Cr, Ni)

#### Alkaline Solutions

- Ammonium Fluoride 40% NH<sub>4</sub>F
- Hydrogen Peroxide 30% H<sub>2</sub>O<sub>2</sub>
- Ammonium Hydroxide 29% NH<sub>4</sub>OH

#### Solvents

- Acetone
- Isopropyl Alcohol
- Methanol

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